

Amendments to the Claims

1. (Previously presented) A chemical vapor deposition method of forming a barium strontium titanate comprising dielectric layer, comprising:

positioning a substrate within a chemical vapor deposition reactor; and
simultaneously a) providing gaseous barium and strontium within the reactor by flowing at least one metal organic precursor to the reactor, b) providing gaseous titanium within the reactor, and c) flowing at least one gaseous oxidizer comprising H₂O to the reactor under conditions effective to deposit a barium strontium titanate comprising dielectric layer on the substrate; and

during the flowing at least one gaseous oxidizer, changing a flow rate of one or more oxidizers to produce a non-homogenous ratio of barium relative to strontium within the dielectric layer.

2. (Original) The method of claim 1 comprising flowing another inorganic oxidizer to the reactor during the deposit.

3. (Original) The method of claim 1 wherein the conditions comprise receipt of the substrate by a susceptor, the susceptor having a temperature of less than or equal to 550°C.

Claims 4-5. (Cancelled)

6. (Previously presented) A chemical vapor deposition method of forming a barium strontium titanate comprising dielectric layer, comprising:

positioning a substrate within a chemical vapor deposition reactor;

simultaneously a) providing gaseous barium and strontium within the reactor by flowing at least one metal organic precursor to the reactor, b) providing gaseous titanium within the reactor, and c) flowing at least one gaseous oxidizer comprising H_2O_2 to the reactor under conditions effective to deposit a barium strontium titanate comprising dielectric layer on the substrate; and

adjusting the flow of the at least one gaseous oxidizer to produce a first portion of the dielectric layer comprising a first ratio of barium relative to strontium, and a second portion of the dielectric layer having a second ratio of barium relative to strontium, the first ratio differing from the second ratio.

7. (Original) The method of claim 6 comprising flowing another inorganic oxidizer to the reactor during the deposit.

8. (Original) The method of claim 6 wherein the conditions comprise receipt of the substrate by a susceptor, the susceptor having a temperature of less than or equal to $550^{\circ}C$.

Claims 9-24. (Cancelled)

25. (Previously presented) The method of claim 1 wherein the at least one metal organic precursor comprises a member selected from the group consisting of Ba(thd)₂, Sr(thd)₂, Ba(methd)₂, Sr(methd)₂, Ba(dpm)₂, and Sr(dpm)₂.

26. (Previously presented) The method of claim 1 wherein the providing gaseous titanium within the reactor comprises flowing at least one member of the group consisting of Ti(dmae)₄, Ti(thd)₂ (O-i-Pr)₂, TiO(dpm)₂, Ti(t-BuO)₂(dpm)₂, and Ti(OCH₃)₂(dpm)₂.

27. (Previously presented) The method of claim 6 wherein the at least one metal organic precursor comprises a member selected from the group consisting of Ba(thd)₂, Sr(thd)₂, Ba(methd)₂, Sr(methd)₂, Ba(dpm)₂, and Sr(dpm)₂.

28. (Previously presented) The method of claim 6 wherein the providing gaseous titanium within the reactor comprises flowing at least one member of the group consisting of Ti(dmae)₄, Ti(thd)₂ (O-i-Pr)₂, TiO(dpm)₂, Ti(t-BuO)₂(dpm)₂, and Ti(OCH₃)₂(dpm)₂.

Claims 29-31 (Cancelled).